

FGW30XS65C

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Discrete IGBT

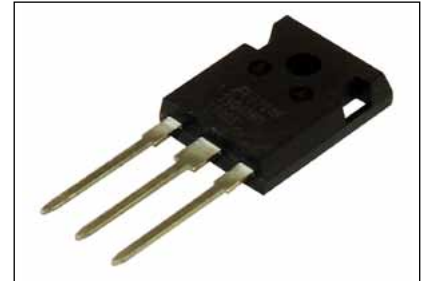
Discrete IGBT (High-Speed XS-series) 650V / 30A

■ Features

- Low power loss
- Low switching surge and noise
- High reliability, high ruggedness (RBSOA etc.)

■ Applications

- Uninterruptible power supply
- PV Power conditioner
- Inverter welding machine



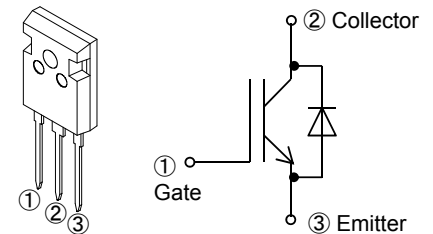
■ Maximum Ratings and Characteristics

● Absolute Maximum Ratings at $T_{vj} = 25^\circ\text{C}$ (unless otherwise specified)

Parameter	Symbol	Value	Unit	Remarks
Collector-Emitter Voltage	V_{CES}	650	V	
Gate-Emitter Voltage	V_{GES}	± 20	V	
Transient Gate-Emitter Voltage		± 30	V	$t_p < 1 \mu\text{s}$
DC Collector Current	$I_{C@25}$	46	A	$T_c = 25^\circ\text{C}$
	$I_{C@100}$	30	A	$T_c = 100^\circ\text{C}$
Pulsed Collector Current	I_{CP}	120	A	Note *1
Turn-Off Safe Operating Area	-	120	A	$V_{CE} \leq 650 \text{ V}$ $T_{vj} \leq 175^\circ\text{C}$
Diode Forward Current	$I_F@25$	48	A	
	$I_F@100$	30	A	
Diode Pulsed Current	I_{FP}	120	A	Note *1
IGBT Max. Power Dissipation	P_{tot_IGBT}	174	W	$T_c = 25^\circ\text{C}$
FWD Max. Power Dissipation	P_{tot_FWD}	131	W	$T_c = 25^\circ\text{C}$
Operating Junction Temperature	T_{vj}	$-40 \sim +175$	$^\circ\text{C}$	
Storage Temperature	T_{stg}	$-55 \sim +175$	$^\circ\text{C}$	

Note *1 : Pulse width limited by $T_{vj\text{max}}$.

■ Equivalent circuit



TO-247-P2

● Electrical Characteristics at $T_{vj} = 25^\circ\text{C}$ (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Zero Gate Voltage Collector Current	I_{CES}	$V_{CE} = 650 \text{ V}$ $V_{GE} = 0 \text{ V}$ $T_{vj} = 25^\circ\text{C}$	-	-	250	μA
		$T_{vj} = 175^\circ\text{C}$	-	-	2	mA
Gate-Emitter Leakage Current	I_{GES}	$V_{CE} = 0 \text{ V}$ $V_{GE} = \pm 20 \text{ V}$	-	-	200	nA
Gate-Emitter Threshold Voltage	$V_{GE(th)}$	$V_{CE} = 20 \text{ V}$ $I_C = 30 \text{ mA}$	3.4	4.0	4.6	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$V_{GE} = 15 \text{ V}$ $I_C = 30 \text{ A}$ $T_{vj} = 25^\circ\text{C}$	1.00	1.35	1.70	V
		$T_{vj} = 125^\circ\text{C}$	-	1.50	-	
		$T_{vj} = 175^\circ\text{C}$	-	1.60	-	
Input Capacitance	C_{ies}	$V_{CE} = 25 \text{ V}$	1250	2500	3750	pF
Output Capacitance	C_{oes}	$V_{GE} = 0 \text{ V}$	30	60	90	pF
Reverse Transfer Capacitance	C_{res}	$f = 1 \text{ MHz}$	13	26	39	pF
Gate Charge	Q_G	$V_{CC} = 520 \text{ V}$ $I_C = 30 \text{ A}$ $V_{GE} = 15 \text{ V}$	65	130	195	nC
Turn-On Delay Time	$t_{d(on)}$	$T_{vj} = 25^\circ\text{C}$	13	25	37	ns
Rise Time	t_r	$V_{CC} = 400 \text{ V}$	5	10	15	ns
Turn-Off Delay Time	$t_{d(off)}$	$I_C = 15 \text{ A}$	84	168	252	ns
Fall Time	t_f	$V_{GE} = 15 \text{ V}$	6	12	18	ns
Turn-On Energy	E_{on}	$R_G = 10 \Omega$	0.14	0.27	0.4	mJ
Turn-Off Energy	E_{off}	Energy loss include "tail" and FWD reverse recovery.	0.11	0.21	0.31	mJ
Turn-On Delay Time	$t_{d(on)}$	$T_{vj} = 150^\circ\text{C}$	13	26	39	ns
Rise Time	t_r	$V_{CC} = 400 \text{ V}$	6	12	18	ns
Turn-Off Delay Time	$t_{d(off)}$	$I_C = 15 \text{ A}$	100	200	300	ns
Fall Time	t_f	$V_{GE} = 15 \text{ V}$	10	20	30	ns
Turn-On Energy	E_{on}	$R_G = 10 \Omega$	0.19	0.38	0.57	mJ
Turn-Off Energy	E_{off}	Energy loss include "tail" and FWD reverse recovery.	0.17	0.34	0.51	mJ
Forward Voltage Drop	V_F	$I_F = 30 \text{ A}$ $T_{vj} = 25^\circ\text{C}$	1.25	1.70	2.15	V
		$T_{vj} = 125^\circ\text{C}$	-	1.78	-	V
		$T_{vj} = 175^\circ\text{C}$	-	1.78	-	V
Diode Reverse Recovery Time	t_{rr}	$V_{CC} = 400 \text{ V}$ $I_F = 15 \text{ A}$ $-di_F/dt = 1200 \text{ A}/\mu\text{s}$ $T_{vj} = 25^\circ\text{C}$	39	78	117	ns
Diode Reverse Recovery Charge	Q_{rr}		0.37	0.74	1.11	μC
Diode Reverse Recovery Time	t_{rr}	$V_{CC} = 400 \text{ V}$ $I_F = 15 \text{ A}$	60	120	180	ns
Diode Reverse Recovery Charge	Q_{rr}	$-di_F/dt = 1000 \text{ A}/\mu\text{s}$ $T_{vj} = 150^\circ\text{C}$	0.6	1.2	1.8	μC

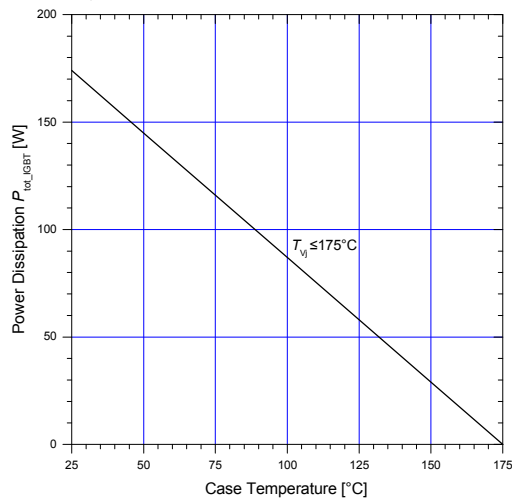
● Thermal Resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal Resistance, Junction-Ambient	$R_{th(j-a)}$	-	-	50	°C/W
Thermal Resistance, IGBT Junction to Case	$R_{th(j-c)}_{IGBT}$	-	-	0.864	°C/W
Thermal Resistance, FWD Junction to Case	$R_{th(j-c)}_{FWD}$	-	-	1.148	°C/W

■ Characteristics (Representative)

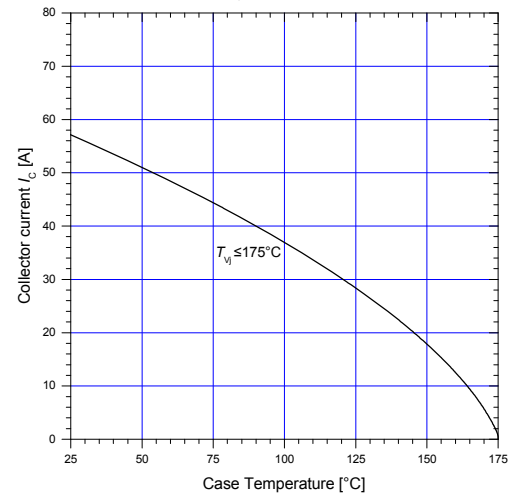
Graph 1
IGBT Power Dissipation vs T_c

$T_{vj} \leq 175^\circ\text{C}$



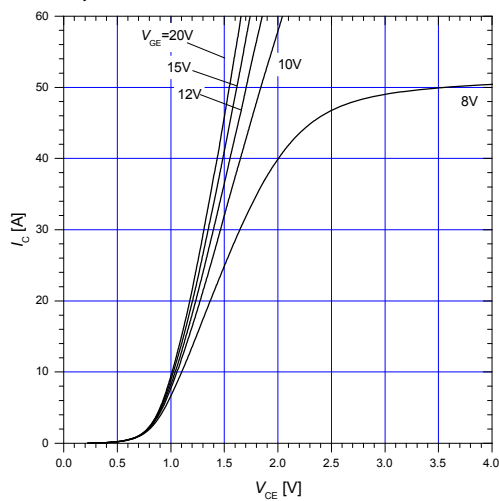
Graph 2
DC Collector Current vs T_c

$V_{GE} \geq +15\text{ V}$, $T_{vj} \leq 175^\circ\text{C}$



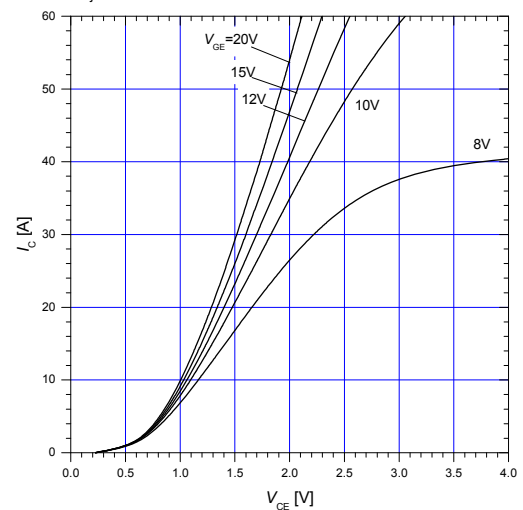
Graph 3
Typical output characteristics

$T_{vj} = 25^\circ\text{C}$



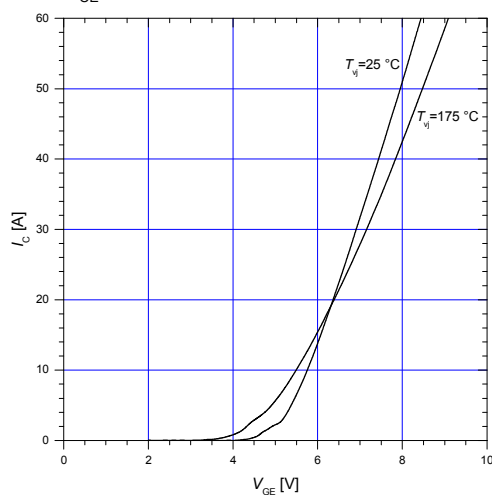
Graph 4
Typical output characteristics

$T_{vj} = 175^\circ\text{C}$



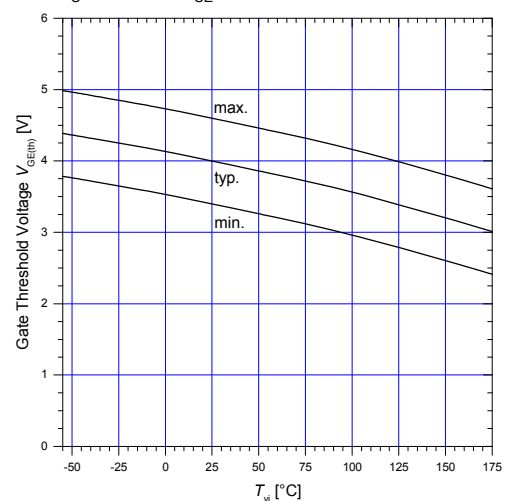
Graph 5
Typical transfer characteristics

$V_{CE} = 20\text{ V}$



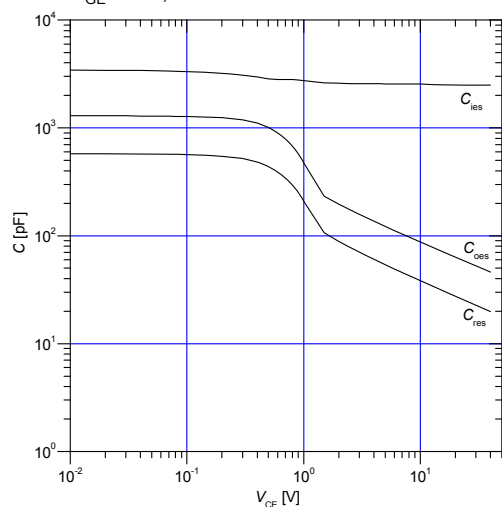
Graph 6
Gate threshold voltage

$I_c = 30\text{ mA}$, $V_{CE} = 20\text{ V}$



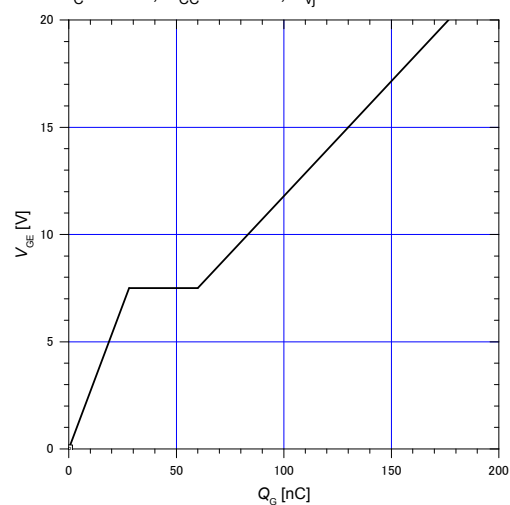
Graph 7
Typical capacitance

$V_{GE} = 0 \text{ V}$, $f = 1 \text{ MHz}$



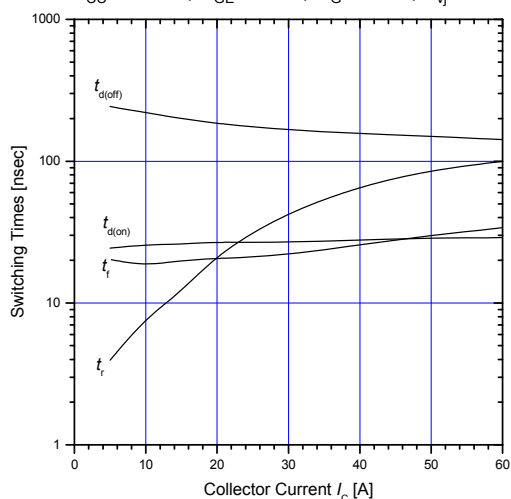
Graph 8
Typical gate charge

$I_C = 30 \text{ A}$, $V_{CC} = 520 \text{ V}$, $T_{vj} = 25^\circ \text{C}$



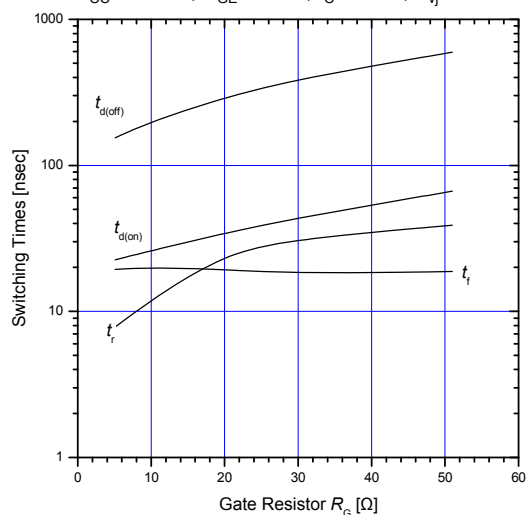
Graph 9
Typical switching times vs. I_C

$V_{CC} = 400 \text{ V}$, $V_{GE} = 15 \text{ V}$, $R_G = 10 \Omega$, $T_{vj} = 150^\circ \text{C}$



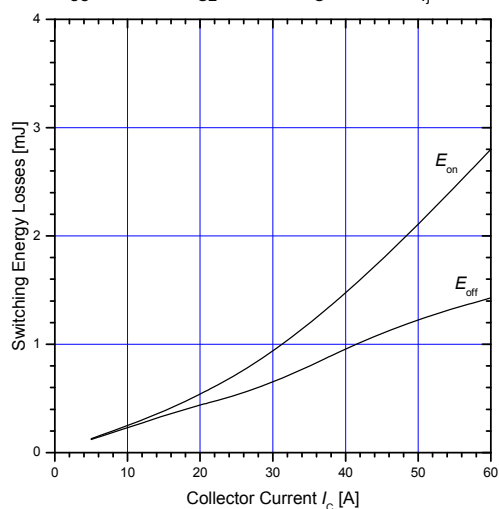
Graph 10
Typical switching times vs. R_G

$V_{CC} = 400 \text{ V}$, $V_{GE} = 15 \text{ V}$, $I_C = 15 \text{ A}$, $T_{vj} = 150^\circ \text{C}$



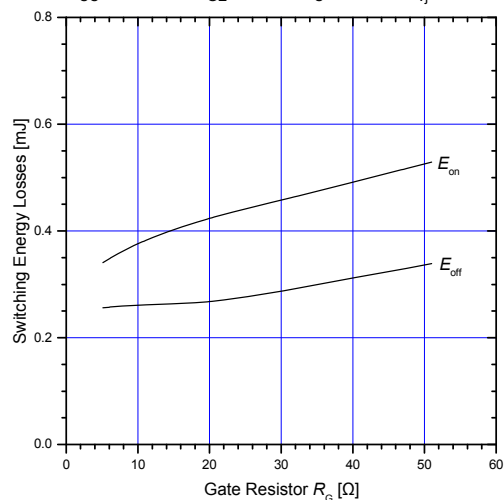
Graph 11
Typical switching losses vs. I_C

$V_{CC} = 400 \text{ V}$, $V_{GE} = 15 \text{ V}$, $R_G = 10 \Omega$, $T_{vj} = 150^\circ \text{C}$

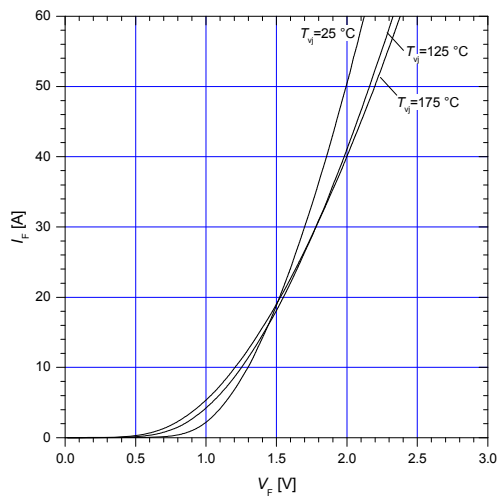


Graph 12
Typical switching losses vs. R_G

$V_{CC} = 400 \text{ V}$, $V_{GE} = 15 \text{ V}$, $I_C = 15 \text{ A}$, $T_{vj} = 150^\circ \text{C}$

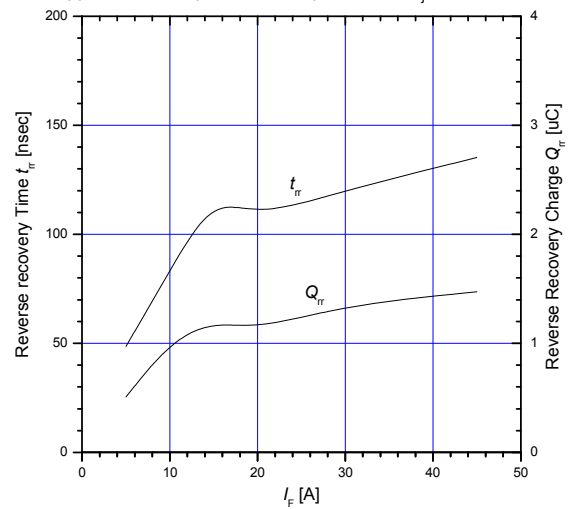


Graph 13
Typical forward characteristics of FWD



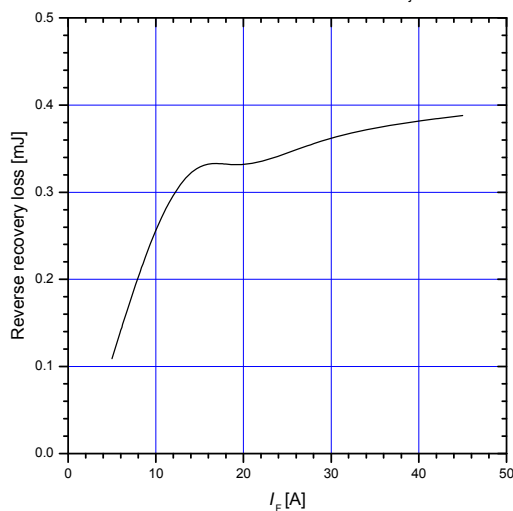
Graph 14
Typical reverse recovery characteristics vs. I_F

$V_{CC} = 400\text{ V}$, $V_{GE} = 15\text{ V}$, $R_G = 10\ \Omega$, $T_{vj} = 150^\circ\text{C}$



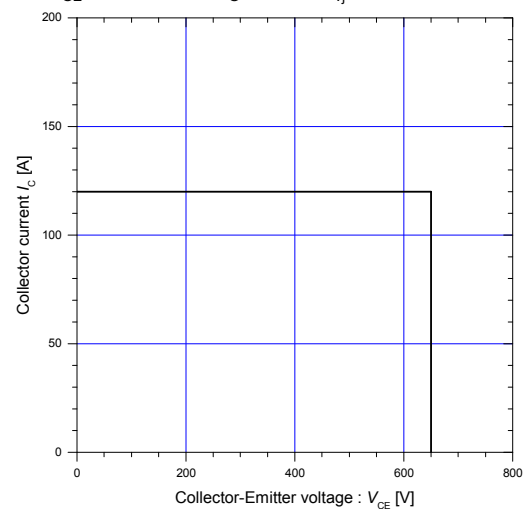
Graph 15
Typical reverse recovery loss vs. I_F

$V_{CC} = 400\text{ V}$, $V_{GE} = 15\text{ V}$, $R_G = 10\ \Omega$, $T_{vj} = 150^\circ\text{C}$



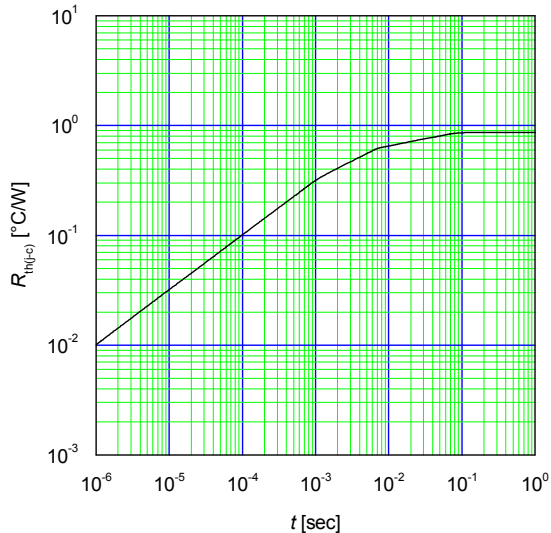
Graph 16
Reverse biased safe operating area

$V_{GE} = 15\text{ V} / 0\text{ V}$, $R_G = 10\ \Omega$, $T_{vj} \leq 175^\circ\text{C}$



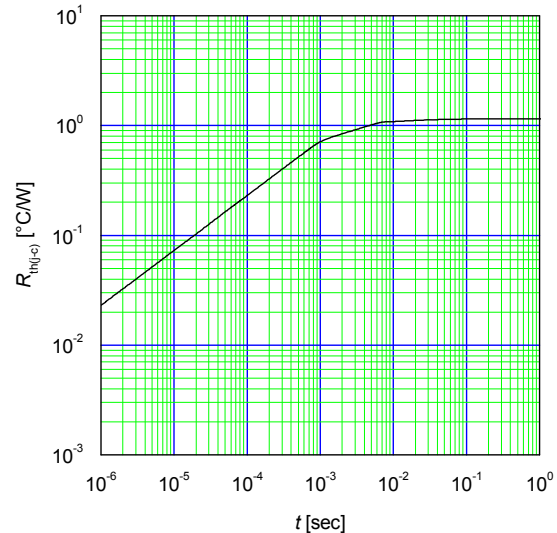
Graph 17
Transient Thermal Impedance of IGBT

$D = 0$

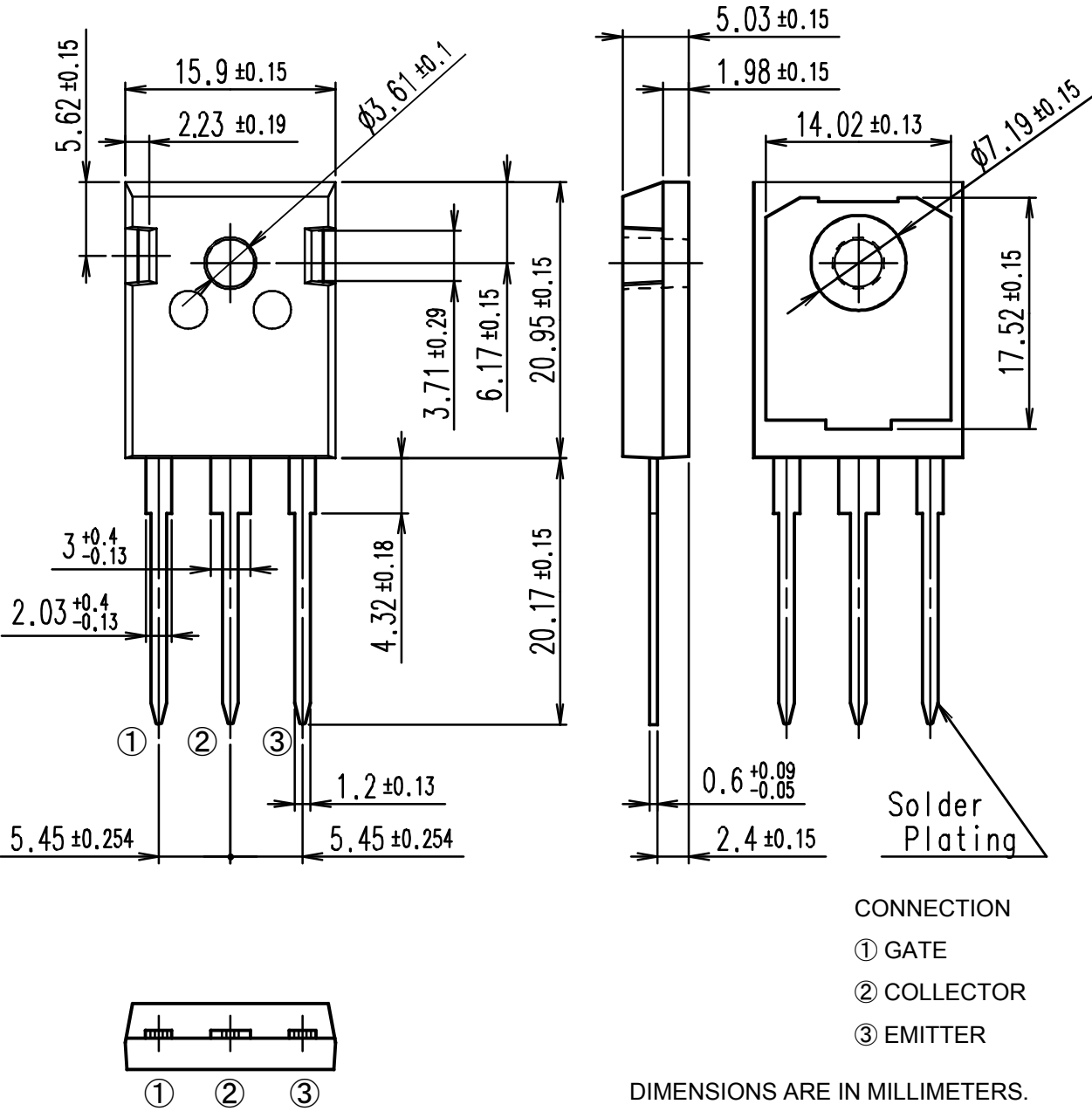


Graph 18
Transient Thermal Impedance of FWD

$D = 0$



Outline Drawings, mm



WARNING

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